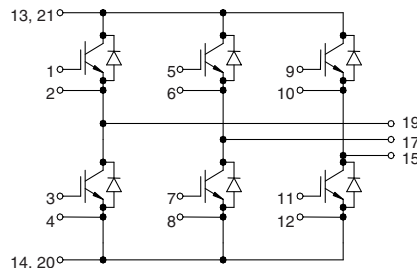


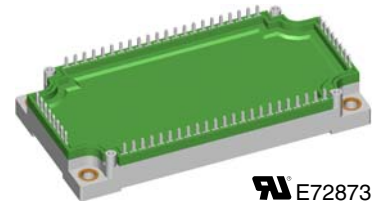
IGBT Modules Sixpack

Short Circuit SOA Capability
Square RBSOA

Preliminary data



$$\begin{aligned} I_{C25} &= 225 \text{ A} \\ V_{CES} &= 600 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 2.0 \text{ V} \end{aligned}$$



See outline drawing for pin arrangement

IGBTs					
Symbol	Conditions	Maximum Ratings			
V_{CES}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	600	V		
V_{GES}		± 20	V		
I_{C25}	$T_C = 25^{\circ}\text{C}$	225	A		
I_{C80}	$T_C = 80^{\circ}\text{C}$	155	A		
RBSOA	$V_{GE} = \pm 15\text{ V}$; $R_G = 1.5\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$	$I_{CM} = 400$ $V_{CEK} \leq V_{CES}$	A		
t_{SC} (SCSOA)	$V_{CE} = V_{CES}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 1.5\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs		
P_{tot}	$T_C = 25^{\circ}\text{C}$	675	W		
Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 200\text{ A}$; $V_{GE} = 15\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.0 2.3	2.5 V	
$V_{GE(th)}$	$I_C = 4\text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.5	1.8 mA mA	
I_{GES}	$V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$			400 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}$; $I_C = 200\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_G = 1.5\ \Omega$		180 50 300 40 4.6 6.3	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25\text{ V}$; $V_{GE} = 0\text{ V}$; $f = 1\text{ MHz}$		9.0	nF
Q_{Gon}		$V_{CE} = 300\text{ V}$; $V_{GE} = 15\text{ V}$; $I_C = 200\text{ A}$		670	nC
R_{thJC}		(per IGBT)			0.18 K/W

Features

- €NPT IGBT technology
- €low saturation voltage
- €low switching losses
- €switching frequency up to 30 kHz
- €square RBSOA, no latch up
- €high short circuit capability
- €positive temperature coefficient for easy parallelling
- €MOS input, voltage controlled
- €ultra fast free wheeling diodes
- €solderable pins for PCB mounting
- €package with copper base plate

Advantages

- €space savings
- €reduced protection circuits
- €package designed for wave soldering

Typical Applications

- €AC motor control
- €AC servo and robot drives
- €power supplies

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	260	A
I_{F80}	$T_C = 80^\circ\text{C}$	165	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 200\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.9 1.5	2.1	V V
I_{RM} t_{rr}	$I_F = 120\text{ A}; di_F/dt = -1000\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	56 100		A ns
R_{thJC}	(per diode)			0.3 K/W

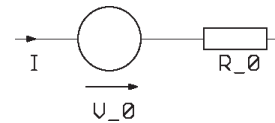
Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	$^\circ\text{C}$
T_{JM}		+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	3 - 6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			1.8	m Ω
d_s	Creepage distance on surface	10		mm
d_A	Strike distance in air	10		mm
R_{thCH}	with heatsink compound		0.01	K/W
Weight		300		g

Equivalent Circuits for Simulation

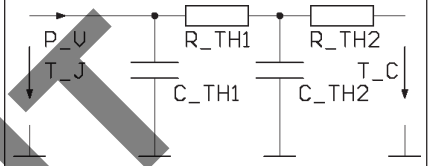
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 1.1\text{ V}; R_0 = 6\text{ m}\Omega$

Free wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.1\text{ V}; R_0 = 2\text{ m}\Omega$

Thermal Response



IGBT (typ.)
 $C_{th1} = 0.397\text{ J/K}; R_{th1} = 0.131\text{ K/W}$
 $C_{th2} = 2.243\text{ J/K}; R_{th2} = 0.049\text{ K/W}$

Free wheeling Diode (typ.)
 $C_{th1} = 0.281\text{ J/K}; R_{th1} = 0.236\text{ K/W}$
 $C_{th2} = 1.945\text{ J/K}; R_{th2} = 0.064\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")

